

150 V (D-S) 175 °C MOSFET

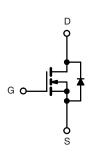
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω)	I <sub>D</sub> (A)			
150	0.052 at V <sub>GS</sub> = 10 V	25			
	0.060 at V <sub>GS</sub> = 6 V	23			

#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % Rg Tested

#### **APPLICATIONS**

• Primary Side Switch



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25 \text{ °C}$ , unless otherwise noted							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage		V <sub>DS</sub>	150	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	v				
Continuous Drain Current (T 175 °C)b	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	25				
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 125 °C		14.5				
Pulsed Drain Current	I <sub>DM</sub>	50	A				
Continuous Source Current (Diode Conduction)	۱ <sub>S</sub>	25					
Avalanche Current	I <sub>AR</sub>	25					
Repetitive Avalanche Energy (Duty Cycle $\leq$ 1 %)	L = 0.1 mH	E <sub>AR</sub>	31	mJ			
Maximum Dawar Discinction	T <sub>C</sub> = 25 °C	PD	136 <sup>b</sup>	w			
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	FD -	3 <sup>a</sup>	vv			
Operating Junction and Storage Temperature Range	÷	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C			

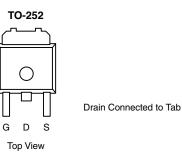
THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
	t ≤ 10 s	R <sub>thJA</sub>	15	18	°C/W		
Junction-to-Ambient <sup>a</sup>	Steady State		40	50			
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.85	1.1			

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.





Ordering Information:

SUD25N15-52-E3 (Lead (Pb)- free)



# SUD25N15-52

N-Channel

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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$ 150				v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2		4	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 150 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			50	P	
		$V_{DS}$ = 150 V, $V_{GS}$ = 0 V, $T_{J}$ = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	50			А	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		0.042	0.052		
	Б	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ A}, \text{ T}_{J} = 125 \text{ °C}$		0.109		0	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ A}, \text{ T}_{J} = 175 ^{\circ}\text{C}$			0.145	Ω	
		$V_{GS} = 6 V, I_D = 5 A$		0.047	0.060		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 25 A		40		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			1725		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz		216			
Reverse Transfer Capacitance	C <sub>rss</sub>			100			
Total Gate Charge <sup>c</sup>	Qg			33	40		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 25 \text{ A}$		9		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			12			
Gate Resistance	Rg		1		3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			15	25		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 3 $\Omega$		70	100		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ 25 A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_\text{g}$ = 2.5 $\Omega$		25	40	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			60	90		
Source-Drain Diode Ratings and Cha	racteristics 7	Γ <sub>C</sub> = 25 °C		•	·		
Pulsed Current	I <sub>SM</sub>				50	А	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 25 A, V <sub>GS</sub> = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 25 A, dl/dt = 100 A/μs		95	140	ns	

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. Independent of operating temperature.

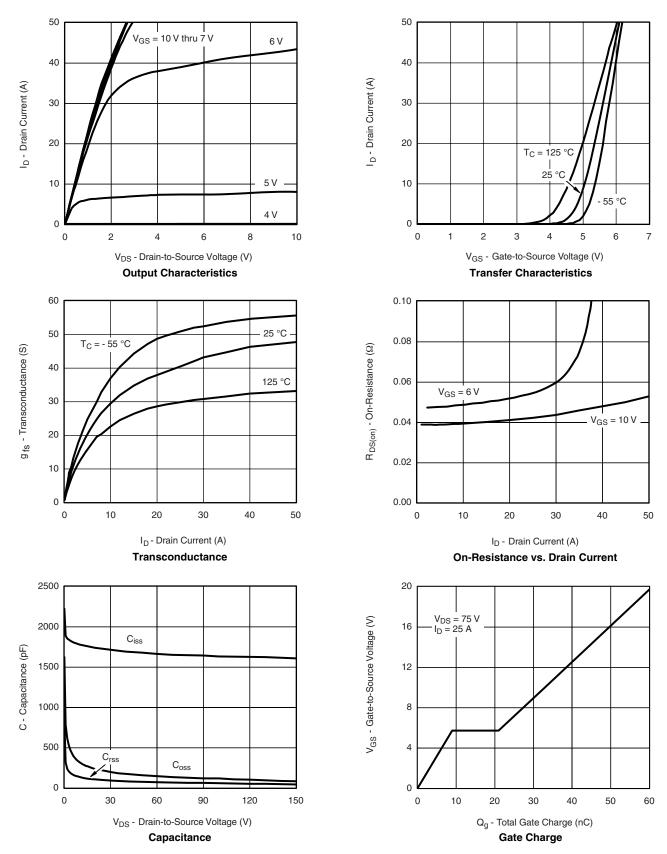
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



# SUD25N15-52 N-Channel

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





## SUD25N15-52 N-Channel

100

10

1

0

0.3

I<sub>S</sub> - Source Current (A)

### 150 V (D-S) 175 °C MOSFET

T<sub>J</sub> = 150 °C

0.6

V<sub>SD</sub> - Source-to-Drain Voltage (V)

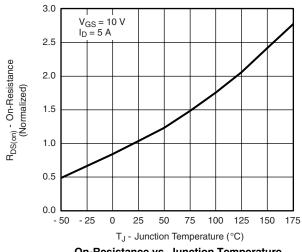
Source-Drain Diode Forward Voltage

T<sub>J</sub> = 25 °C

0.9

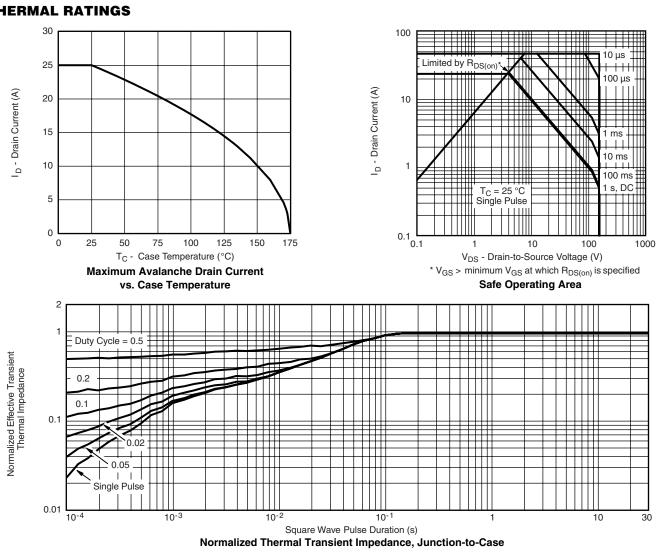
1.2

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



**On-Resistance vs. Junction Temperature** 

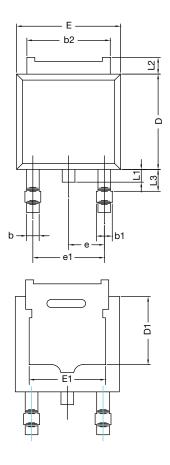


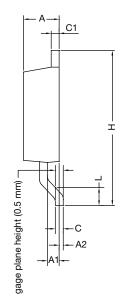




### **SUD25N15-52** N-Channel 150 V (D-S) 175 °C MOSFET

#### TO-252AA CASE OUTLINE





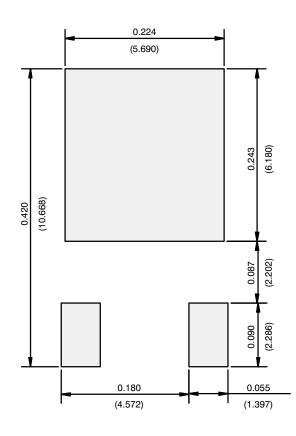
	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
E	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090	BSC	
e1	4.57	BSC	0.180	BSC	
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

#### Note

• Dimension L3 is for reference only.



#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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